Amendments to the Specification:

Please replace the paragraph beginning at page 3, line 19, with the following rewritten paragraph:

In one aspect of an ECMPR process, a workpiece-surface-influencing-device (WSID) such as a mask, pad or a sweeper is used during at least a portion of the electrotreatment process when there is close proximity, either physical contact or a slight spacing, with physical contact preferred, and relative motion between the workpiece surface and the WSID. Descriptions of various planar deposition and planar etching methods i.e. ECMPR approaches and apparatus can be found in the following patents and pending applications, all commonly owned by the assignee of the present invention. U.S. Patent No. 6,176,992 entitled "Method and Apparatus for Electrochemical Mechanical Deposition." U. S. Application No. 09/740,701 entitled "Plating Method and Apparatus that Creates a Differential Between Additive Disposed on a Top Surface and a Cavity Surface of a Workpiece Using an External Influence," filed on December 18, 2000, and U.S. Application No. 09/961,193 ~~application~~ filed on September 20, 2001 ~~with attorney's docket No.42496/269244~~, entitled "Plating Method and Apparatus for Controlling Deposition on Predetermined Portions of a Workpiece". These methods can deposit metals in and over cavity sections on a workpiece in a planar manner. They also have the capability of yielding novel structures with excess amount of metals selectively over the features irrespective of their size, if desired.

Please replace the paragraph beginning at page 18, line 6, with the following rewritten paragraph:

The present invention can also be used during manufacture of conductive networks requiring formation of narrow and large gaps through a mask layer coated on a substrate and filling them with a conductive material such as copper using the ECMD process. One such example is described in US ~~Provisional~~ Application No. 10/282,976 ~~60/_____ bearing attorney reference 042496/0269271~~, entitled Method and Structure for Thru-Mask Contact Electrodeposition, filed on October 28, 2002 ~~27, 2001~~, owned by the assignee of the present invention. As shown in Figures 10A-10B, a substrate 180 is first coated with a barrier layer 182 and then with a copper seed layer 184. A resist layer 186 is formed on the seed layer 184 and defined and etched to form various features such as vias 188 and trenches 190. The resist material may be soft or hard baked organic materials, it could be inorganic materials such as silicon oxide, alumina, sapphire or another material. The resist material may also be a low or high dielectric constant material. In the context of this embodiment, a resist material is hereby defined as that material that copper or any metal of interest will not nucleate on without a seed layer coating. Similar to the embodiment described with Figures 8A-8C, Figure 10A shows features that are partially filled using the ECMD process. In this embodiment as the features 188, 190 are filled with a copper layer 191, input beam 192 from a source 194 arrives at the surface of the substrate under the same angle of incidence, with a known intensity. Because of the surface roughness, output beams 196 are randomly scattered and only a few beams are detected by the sensor 198. Therefore, if the input beam 192 has a predetermined intensity, the intensity loss, which is detected by the sensor 198, indicates the surface roughness. The ECMD process is continued to plate copper. As shown in Figure 10B, as a copper layer completely fills the features and the copper layer 191 becomes planar, the intensity of the output beam 196 that is detected by the sensor 198 increases. Once the planar surface is obtained, the ECMD process is halted.

Please replace the paragraph beginning at page 19, line 11, with the following rewritten paragraph:

Figures 11A-11B shows an ECMPR system 200 using a belt WSID 202. An example of such belt WSID is described in US ~~provisional application~~ Application No. 10/288,558 ~~with Attorney's Docket No. 042496/0269271~~, entitled Electrochemical Mechanical Processing with Advancible Sweeper, filed November 4, 2002 ~~2, 2001~~, commonly owned by the assignee of the present invention. The belt WSID 202 is extended between a supply spool 204 and storage spool 206 and moved by a moving mechanism (not shown). During the process, a wafer 208 is held by the carrier head 210 in close proximity of the belt WSID such that a process solution 212, such as an electrolyte, flowing through a porous support plate 213 and channels 214 in the belt WSID wets the front surface of the wafer. The process solution and an electrode 215 that is immersed in the solution are kept in a container 216. The wafer processed over a predetermined area or a process area 218 of the belt WSID. As the belt is tensioned over an upper surface of the porous support plate, a top compressible layer 220 of the support plate pushes the belt upward. The process area is renewed by advancing the belt WSID such that a used process area is replaced by a fresh process area by rolling the used process area over the storage spool and thereby drawing fresh process area from the supply spool. During the process, the wafer carrier can move the wafer on or above the belt WSID laterally and rotate about the rotation axis z of the wafer carrier. The belt WSID of the present invention can also be moved laterally while the wafer is moved on it by the carrier head.